

# PEMD3; PIMD3; PUMD3

NPN/PNP resistor-equipped transistors;  
R1 = 10 k $\Omega$ , R2 = 10 k $\Omega$

Rev. 09 — 18 May 2005

Product data sheet

## 1. Product profile

### 1.1 General description

NPN/PNP Resistor-Equipped Transistors (RET).

Table 1: Product overview

Type number	Package		PNP/PNP complement	NPN/PNP complement
	Philips	JEITA		
PEMD3	SOT666	-	PEMB11	PEMH11
PIMD3	SOT457	SC-74	-	-
PUMD3	SOT363	SC-88	PUMB11	PUMH11

### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

### 1.4 Quick reference data

Table 2: Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	50	V
I <sub>O</sub>	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		7	10	13	k $\Omega$
R2/R1	bias resistor ratio		0.8	1	1.2	

## 2. Pinning information

Table 3: Pinning

Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1		
3	output (collector) TR2		
4	GND (emitter) TR2		
5	input (base) TR2		
6	output (collector) TR1		

## 3. Ordering information

Table 4: Ordering information

Type number	Package		
	Name	Description	Version
PEMD3	-	plastic surface mounted package; 6 leads	SOT666
PIMD3	SC-74	plastic surface mounted package; 6 leads	SOT457
PUMD3	SC-88	plastic surface mounted package; 6 leads	SOT363

## 4. Marking

Table 5: Marking codes

Type number	Marking code <sup>[1]</sup>
PEMD3	D3
PIMD3	M7
PUMD3	D*3

- [1] \* = -: made in Hong Kong  
 \* = p: made in Hong Kong  
 \* = t: made in Malaysia  
 \* = W: made in China

## 5. Limiting values

**Table 6: Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
<b>Per transistor; for the PNP transistor with negative polarity</b>						
$V_{CBO}$	collector-base voltage	open emitter	-	50	V	
$V_{CEO}$	collector-emitter voltage	open base	-	50	V	
$V_{EBO}$	emitter-base voltage	open collector	-	10	V	
$V_I$	input voltage TR1					
		positive	-	+40	V	
		negative	-	-10	V	
	input voltage TR2					
		positive	-	+10	V	
		negative	-	-40	V	
$I_O$	output current (DC)		-	100	mA	
$I_{CM}$	peak collector current		-	100	mA	
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$				
	SOT363		[1]	-	200	mW
	SOT457		[2]	-	300	mW
	SOT666		[1] [3]	-	200	mW
$T_{stg}$	storage temperature		-65	+150	°C	
$T_j$	junction temperature		-	150	°C	
$T_{amb}$	ambient temperature		-65	+150	°C	
<b>Per device</b>						
$P_{tot}$	total power dissipation	$T_{amb} \leq 25\text{ °C}$				
	SOT363		[1]	-	300	mW
	SOT457		[2]	-	600	mW
	SOT666		[1] [3]	-	300	mW

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB with 65 μm copper strip line, standard footprint.

[3] Reflow soldering is the only recommended soldering method.

## 6. Thermal characteristics

**Table 7: Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Per transistor</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		[1]	-	625	K/W
	SOT457		[2]	-	417	K/W
	SOT666		[1][3]	-	625	K/W
<b>Per device</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		[1]	-	416	K/W
	SOT457		[2]	-	208	K/W
	SOT666		[1][3]	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB with 65 μm copper strip line, standard footprint.

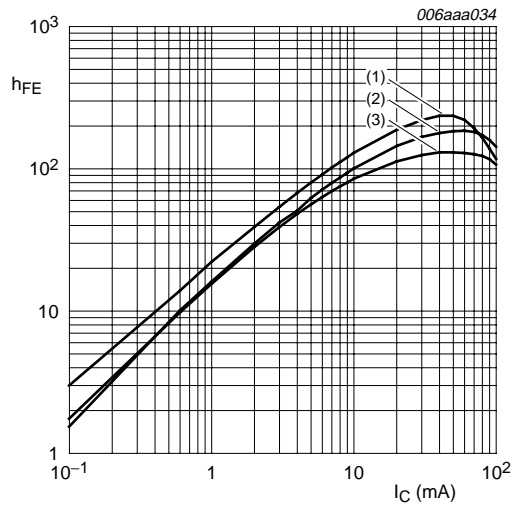
[3] Reflow soldering is the only recommended soldering method.

## 7. Characteristics

**Table 8: Characteristics**

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

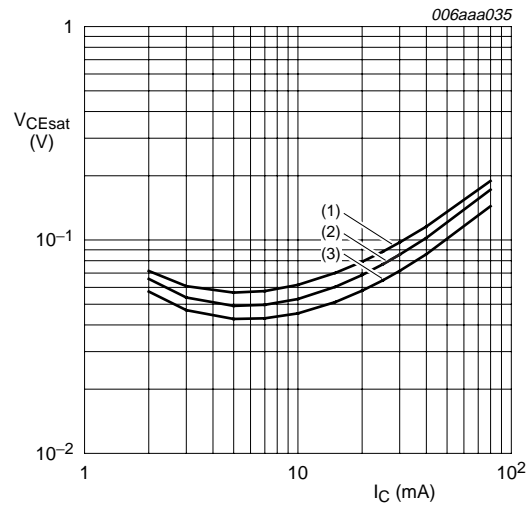
Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
<b>Per transistor; for the PNP transistor with negative polarity</b>							
$I_{CBO}$	collector-base cut-off current	$V_{CB} = 50\text{ V}; I_E = 0\text{ A}$	-	-	100	nA	
$I_{CEO}$	collector-emitter cut-off current	$V_{CE} = 30\text{ V}; I_B = 0\text{ A}$	-	-	1	μA	
		$V_{CE} = 30\text{ V}; I_B = 0\text{ A}; T_j = 150\text{ °C}$	-	-	50	μA	
$I_{EBO}$	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	400	μA	
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}; I_C = 5\text{ mA}$	30	-	-		
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	-	150	mV	
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5\text{ V}; I_C = 100\text{ μA}$	-	1.1	0.8	V	
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3\text{ V}; I_C = 10\text{ mA}$	2.5	1.8	-	V	
R1	bias resistor 1 (input)		7	10	13	kΩ	
R2/R1	bias resistor ratio		0.8	1	1.2		
$C_c$	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_C = 0\text{ A}; f = 1\text{ MHz}$	-	-	-		
			TR1 (NPN)	-	-	2.5	pF
			TR2 (PNP)	-	-	3	pF



$V_{CE} = 5 \text{ V}$

- (1)  $T_{amb} = 150 \text{ }^\circ\text{C}$
- (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$
- (3)  $T_{amb} = -40 \text{ }^\circ\text{C}$

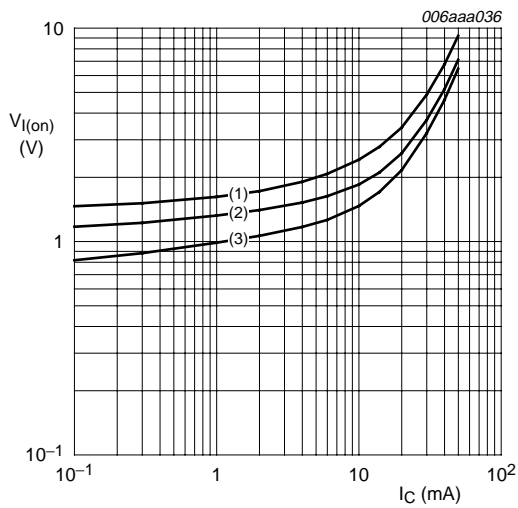
**Fig 1. TR1 (NPN): DC current gain as a function of collector current; typical values**



$I_C/I_B = 20$

- (1)  $T_{amb} = 100 \text{ }^\circ\text{C}$
- (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$
- (3)  $T_{amb} = -40 \text{ }^\circ\text{C}$

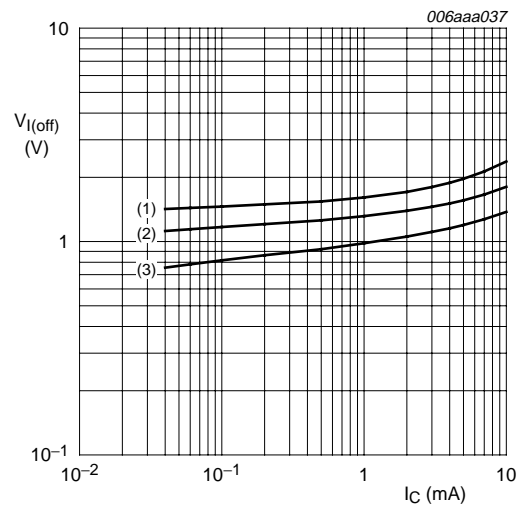
**Fig 2. TR1 (NPN): Collector-emitter voltage as a function of collector current; typical values**



$V_{CE} = 0.3 \text{ V}$

- (1)  $T_{amb} = -40 \text{ }^\circ\text{C}$
- (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$
- (3)  $T_{amb} = 100 \text{ }^\circ\text{C}$

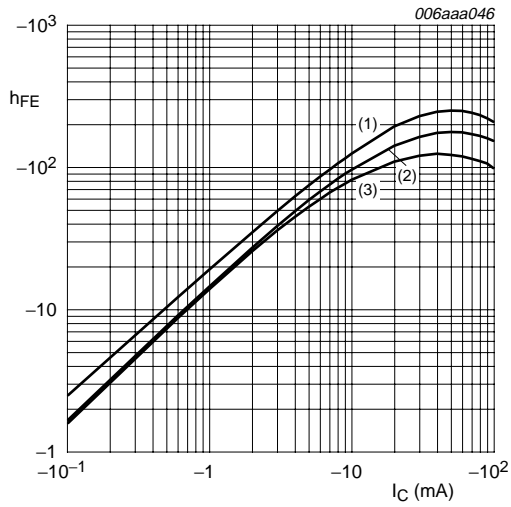
**Fig 3. TR1 (NPN): On-state input voltage as a function of collector current; typical values**



$V_{CE} = 5 \text{ V}$

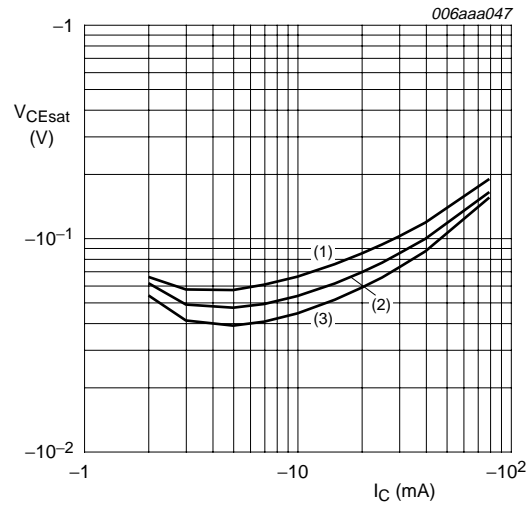
- (1)  $T_{amb} = -40 \text{ }^\circ\text{C}$
- (2)  $T_{amb} = 25 \text{ }^\circ\text{C}$
- (3)  $T_{amb} = 100 \text{ }^\circ\text{C}$

**Fig 4. TR1 (NPN): Off-state input voltage as a function of collector current; typical values**



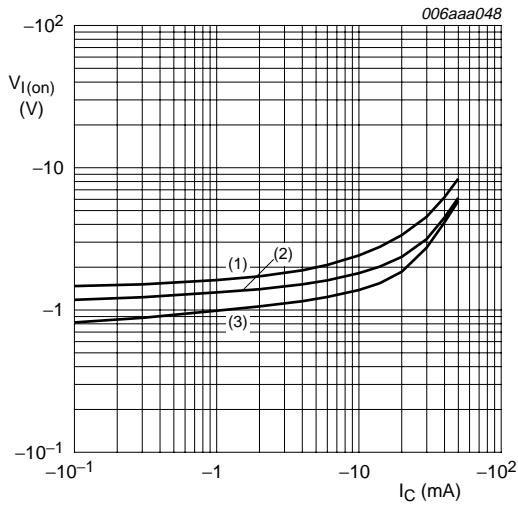
$V_{CE} = -5\text{ V}$   
 (1)  $T_{amb} = 150\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -40\text{ °C}$

**Fig 5. TR2 (PNP): DC current gain as a function of collector current; typical values**



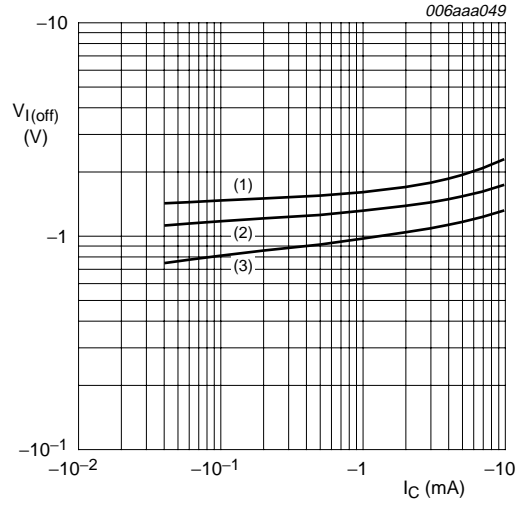
$I_C/I_B = 20$   
 (1)  $T_{amb} = 100\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = -40\text{ °C}$

**Fig 6. TR2 (PNP): Collector-emitter voltage as a function of collector current; typical values**



$V_{CE} = -0.3\text{ V}$   
 (1)  $T_{amb} = -40\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = 100\text{ °C}$

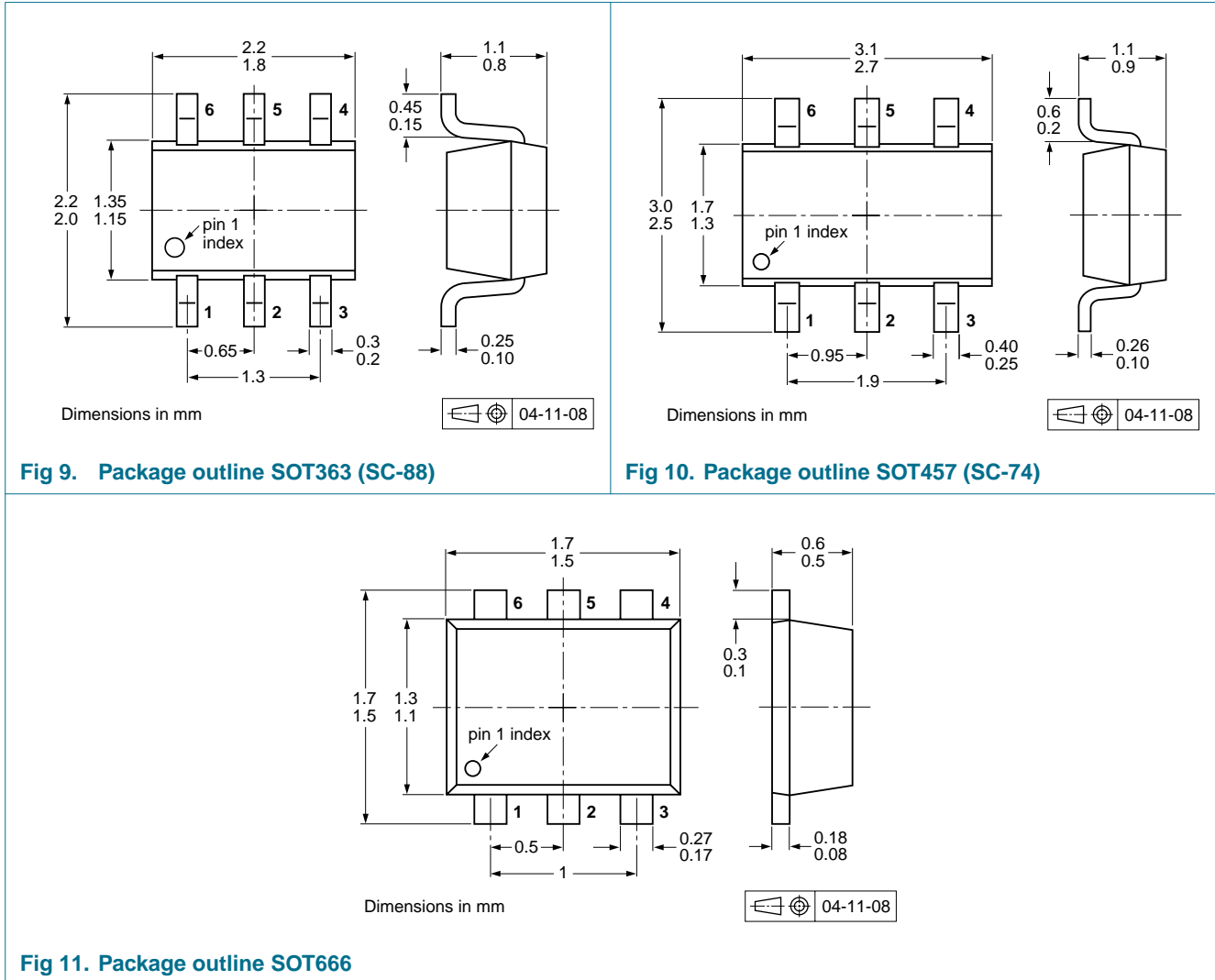
**Fig 7. TR2 (PNP): On-state input voltage as a function of collector current; typical values**



$V_{CE} = -5\text{ V}$   
 (1)  $T_{amb} = -40\text{ °C}$   
 (2)  $T_{amb} = 25\text{ °C}$   
 (3)  $T_{amb} = 100\text{ °C}$

**Fig 8. TR2 (PNP): Off-state input voltage as a function of collector current; typical values**

**8. Package outline**



## 9. Packing information

**Table 9: Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code. [\[1\]](#)

Type number	Package	Description	Packing quantity			
			3000	4000	8000	10000
PEMD3	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PIMD3	SOT457	4 mm pitch, 8 mm tape and reel; T1 <a href="#">[2]</a>	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2 <a href="#">[3]</a>	-125	-	-	-165
PUMD3	SOT363	4 mm pitch, 8 mm tape and reel; T1 <a href="#">[2]</a>	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2 <a href="#">[3]</a>	-125	-	-	-165

[1] For further information and the availability of packing methods, see [Section 15](#).

[2] T1: normal taping

[3] T2: reverse taping

## 10. Revision history

**Table 10: Revision history**

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PEMD3_PIMD3_ PUMD3_9	20050518	Product data sheet	-	9397 750 14517	PEMD3_PIMD3_ PUMD3_8
Modifications:	<ul style="list-style-type: none"><li>• <a href="#">Table 1</a>: EIAJ amended to JEITA</li><li>• <a href="#">Table 9</a>: Packing method (2 mm pitch) for SOT666 added</li><li>• <a href="#">Section 14</a>: added</li></ul>				
PEMD3_PIMD3_ PUMD3_8	20041206	Product data sheet	-	9397 750 13294	PEMD3_PUMD3_7

## 11. Data sheet status

Level	Data sheet status <sup>[1]</sup>	Product status <sup>[2] [3]</sup>	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

[1] Please consult the most recently issued data sheet before initiating or completing a design.

[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

## 12. Definitions

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

**Limiting values definition** — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

**Application information** — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

## 13. Disclaimers

**Life support** — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors

## 15. Contact information

For additional information, please visit: <http://www.semiconductors.philips.com>

For sales office addresses, send an email to: [sales.addresses@www.semiconductors.philips.com](mailto:sales.addresses@www.semiconductors.philips.com)

customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

**Right to make changes** — Philips Semiconductors reserves the right to make changes in the products - including circuits, standard cells, and/or software - described or contained herein in order to improve design and/or performance. When the product is in full production (status 'Production'), relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN). Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no license or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

## 14. Trademarks

**Notice** — All referenced brands, product names, service names and trademarks are the property of their respective owners.

## 16. Contents

---

<b>1</b>	<b>Product profile</b> .....	<b>1</b>
1.1	General description .....	1
1.2	Features .....	1
1.3	Applications .....	1
1.4	Quick reference data .....	1
<b>2</b>	<b>Pinning information</b> .....	<b>2</b>
<b>3</b>	<b>Ordering information</b> .....	<b>2</b>
<b>4</b>	<b>Marking</b> .....	<b>2</b>
<b>5</b>	<b>Limiting values</b> .....	<b>3</b>
<b>6</b>	<b>Thermal characteristics</b> .....	<b>4</b>
<b>7</b>	<b>Characteristics</b> .....	<b>4</b>
<b>8</b>	<b>Package outline</b> .....	<b>7</b>
<b>9</b>	<b>Packing information</b> .....	<b>8</b>
<b>10</b>	<b>Revision history</b> .....	<b>9</b>
<b>11</b>	<b>Data sheet status</b> .....	<b>10</b>
<b>12</b>	<b>Definitions</b> .....	<b>10</b>
<b>13</b>	<b>Disclaimers</b> .....	<b>10</b>
<b>14</b>	<b>Trademarks</b> .....	<b>10</b>
<b>15</b>	<b>Contact information</b> .....	<b>10</b>



© Koninklijke Philips Electronics N.V. 2005

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Date of release: 18 May 2005  
Document number: 9397 750 14517

Published in The Netherlands